

250V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = +25°C	
-250V	14Ω @ V _{GS} = 10V	-265mA	

Description

This new generation trench MOSFET features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Applications

- · Earth Recall and Dialling Switches
- · Electronic Hook Switches
- · High Voltage Power MOSFET Drivers
- · Telecom Call Routers
- Solid State Relays

Features and Benefits

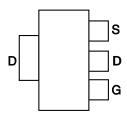
- High Voltage
- Low On-resistance
- Fast Switching Speed
- Low Gate Drive
- Low Threshold
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

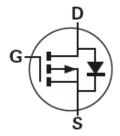
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.112 grams (Approximate)







Pin Out - Top



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZVP4525GTA	ZVP4525	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223

ZVP4525 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5 = 2015) WW or $\overline{W}W$ = Week Code (01~53)

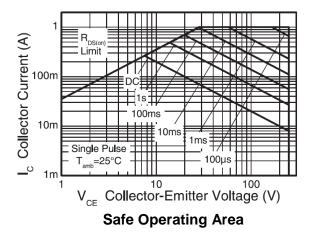


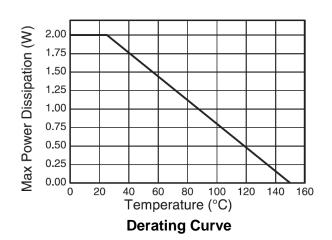
Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

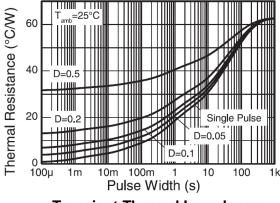
Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-250	V
Gate-Source Voltage	V_{GSS}	±40	V
Continuous Drain Current $@V_{GS} = 10V$; $T_A = +25$ °C (Note 5) $@V_{GS} = 10V$; $T_A = +70$ °C (Note 5)	ID	-265 -212	mA
Pulsed Drain Current (Note 7)	I _{DM}	-1	A
Continuous Source Current (Body Diode)	Is	-0.75	A
Pulsed Source Current (Body Diode)	I _{SM}	-1	A

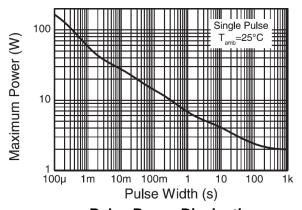
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation at T _A = +25°C (Note 5)	P _D	2.0	W
Linear Derating Factor	Гυ	16	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ heta JA}$	63	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	26	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C









Transient Thermal Impedance

Pulse Power Dissipation



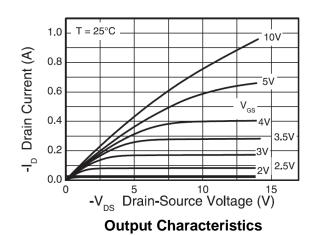
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

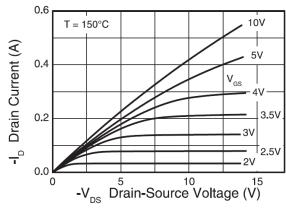
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-250	-285	-	V	$V_{GS} = 0V$, $I_D = -1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-30	-500	nΑ	$V_{DS} = -250V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	±1	±100	nA	$V_{GS} = \pm 40V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	-0.8	-1.5	-2.0	V	$V_{DS} = V_{GS}$, $I_D = -1mA$	
Statio Drain Source On Registeres (Note 9)	В	-	10	14	Ω	V _{GS} = -10V, I _D = -200mA	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	-	13	18	Ω	V _{GS} = -3.5V, I _D = -100mA	
Forward Transconductance (Note 10)	g fs	80	200	-	mS	$V_{DS} = -10V, I_D = -0.15A$	
Diode Forward Voltage (Note 8)	V _{SD}	-	-	0.97	V	$I_S = -200 \text{mA}, V_{GS} = 0 \text{V}, T_J = +25 ^{\circ}\text{C}$	
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 10)	C _{iss}	-	73	-	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance (Note 10)	Coss	-	12.8	-	pF		
Reverse Transfer Capacitance (Note 10)	C _{rss}	-	3.91	-	pF	- I = I.ONIAZ	
Total Gate Charge (Notes 9 &10)	Qg	-	2.45	3.45	nC		
Gate-Source Charge (Notes 9 &10)	Q _{gs}	-	0.22	0.31	nC	$V_{GS} = -10V, V_{DS} = -25V$ $I_{D} = -200mA$	
Gate-Drain Charge (Notes 9 &10)	Q _{gd}	-	0.45	0.63	nC	I _D = -200mA	
Turn-On Delay Time (Notes 9 & 10)	t _{D(ON)}	-	1.53	-	ns		
Turn-On Rise Time (Notes 9 & 10)	t _R	-	3.78	-	ns	$V_{DD} = -30V$, $I_D = -200$ mA, $V_{GS} = -10V$, $R_G = 50\Omega$	
Turn-Off Delay Time (Notes 9 & 10)	t _{D(OFF)}	-	17.5	-	ns		
Turn-Off Fall Time (Notes 9 & 10)	t _F	-	7.85	-	ns		
Reverse Recovery Time (Note 10)	t _{RR}	-	205	290	ns	I _F = -200mA, di/dt = 100A/µs,	
Reverse Recovery Charge (Note 10)	Qrr	-	21	29	nC	T _J = +25°C	

Notes:

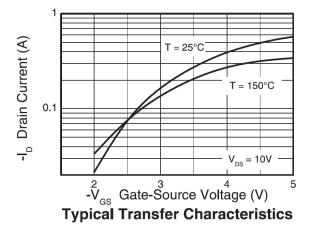
- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
 6. For a device surface mounted on FR4 PCB measured at t ≤ 5 secs.
 7. Repetitive rating 25mm x 25mm FR4 PCB, D=0.02 pulse width=300µs pulse width limited by maximum junction temperature.

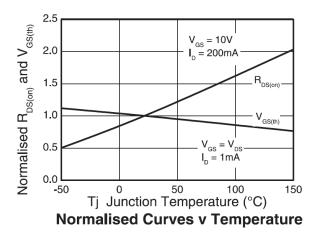
- 8. Measured under pulsed conditions. Pulse width \leq 300µs; duty cycle \leq 2%.
- 9. Switching characteristics are independent of operating junction temperature.
- 10. For design aid only, not subject to production testing.

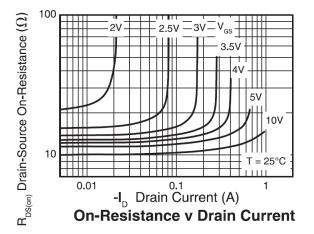


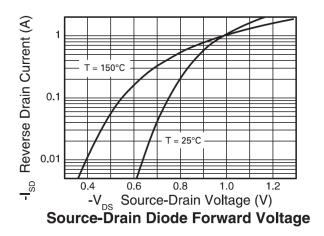


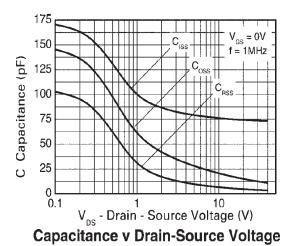


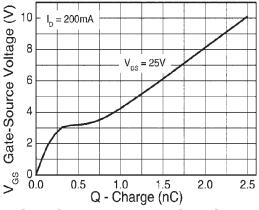










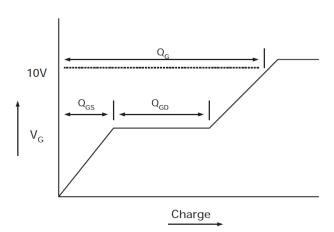


Gate-Source Voltage v Gate Charge

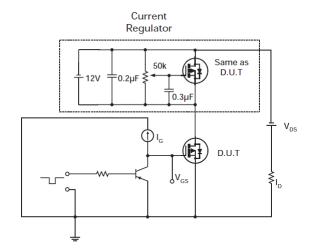
March 2015



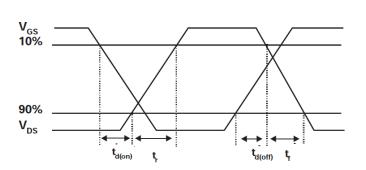
Test Circuits



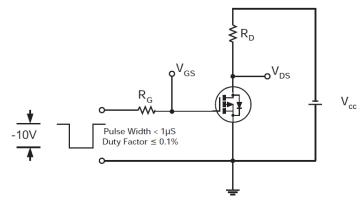
Basic Gate Charge Waveform



Gate Charge Test Circuit



Switching Time Waveforms

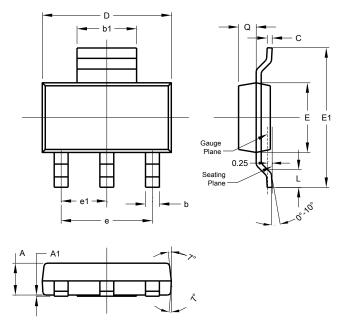


Switching Time Test Circuit



Package Outline Dimensions

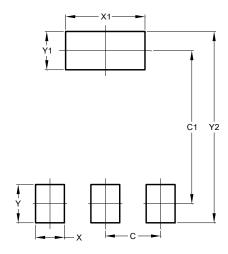
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223				
Dim	Min	Max	Тур	
Α	1.55	1.65	1.60	
A1	0.010	0.15	0.05	
b	0.60	0.80	0.70	
b1	2.90	3.10	3.00	
С	0.20	0.30	0.25	
D	6.45	6.55	6.50	
Е	3.45	3.55	3.50	
E1	6.90	7.10	7.00	
е	-	-	4.60	
e1	-	-	2.30	
L	0.85	1.05	0.95	
ø	0.84	0.94	0.89	
All Dimensions in mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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